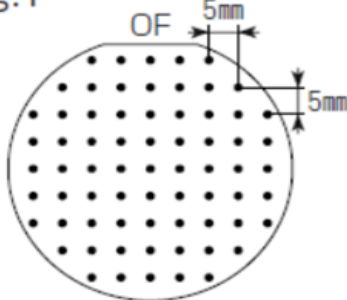


# GaAs Single Crystal Wafers for Laser Diodes

## Standard Specifications(VB)

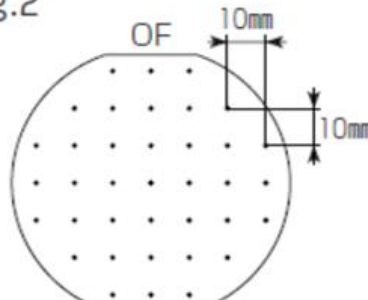
Conduction Type	n-Type		
Growth Method·Dopant	VB·Si		
Carrier Concentration( $\text{cm}^{-3}$ )	$0.7 \sim 4 \times 10^{18}$		
Resistivity( $\Omega \cdot \text{cm}$ )	$1 \sim 6 \times 10^{-3}$		
Mobility( $\text{cm}^2/\text{V} \cdot \text{sec}$ )	$1.2 \sim 3 \times 10^3$		
EPD Average( $\text{cm}^{-2}$ )	$\leq 1 \times 10^2$	$\leq 5 \times 10^2$	
Measuring Points of EPD	Fig.2	Fig.3	Fig.4
Diameter(mm)	$76.0 \pm 0.3$	$100.0 \pm 0.3$	$150.0 \pm 0.3$
OF(mm)(Fig. 5)	$22.0 \pm 2.0$	$32.5 \pm 1.0$	Notch
	Natural Cleavage		
IF(mm)(Fig. 5)	$12.0 \pm 1.0$	$18.0 \pm 1.0$	
Edge Rounding(mmR)	0.25(Conform to SEMI Standards)		
Thickness( $\mu\text{m}$ )	$450 \pm 25$	$450/625 \pm 25$	$675 \pm 25$
Orientation	$(100) \pm 0.3^\circ$ , $(100)2^\circ \sim 15^\circ \text{off} \pm 0.3^\circ$		
Surface Finish	P/LE	P/P	
Surface Clean	SC+(Super Clean Plus)		
Flatness	Refer to other specification		
Package	Cassette / Individual Container		Cassette

Fig.1



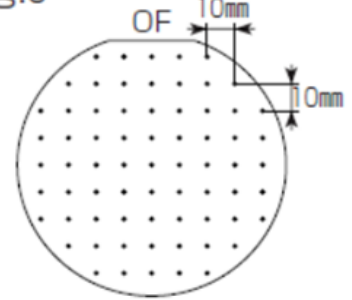
69 Points

Fig.2



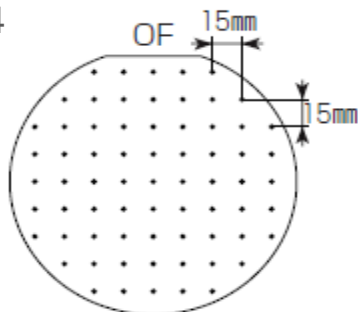
37 Points

Fig.3



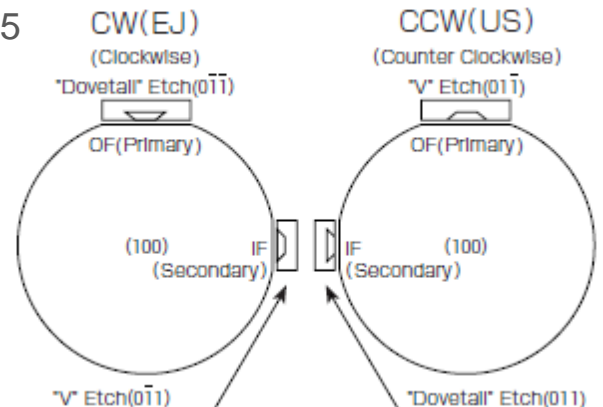
69 Points

Fig.4



69 Points

Fig.5



## Attached Data

- Standard : Carrier Concentration, Resistivity, Mobility, EPD Average, Diameter, OF, IF, Thickness(min.~max.)